ocket No.:

GR 99 P 2591

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Date: August 29, 2001

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**Applicant** 

Gerald Deboy et al.

Applic. No.

09/838,743 V

Filed

April 19, 2001

Title

Vertically structured power semiconductor component

Group Art Unit

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents and Trademarks, Washington, D. C. 20231

Sir:

Al

Preliminary to examination, kindly amend the above-identified application as follows:

## In the Abstract:

On page 29, replace the entire paragraph with the following paragraph:

A vertically structured semiconductor power component is described. A layer thickness of a substrate of the power module between a pn junction and a metallized back is chosen in such a manner that a space charge region produced in the semiconductor component extends as far as the back when a blocking voltage between a source and a drain electrode is applied before a field strength produced by the applied blocking voltage reaches a critical value.